G. Device & Process Modeling, Simulation and Reliability 분과
[TD2-G] Atomistic Modeling

TD2-G-1 10:45~11:15	**[초청]** **Atomistic Molecular Dynamics Simulation for Semiconductor Processes Using Neural Network Potentials** Dongheon Lee, Kyeongpung Lee, Wonseok Jeong, Kyuhyun Lee, Dongsun Yoo, and Seungwu Han *Department of Materials Science and Engineering, Seoul National University*
TD2-G-2 11:15~11:30	**Investigation into the Effects of Ag Insertion Layer in TiN/SiN$_x$/TiN ReRAM through Monte Carlo Simulation** Yeon-Joon Choi[1], Min-Hwi Kim[1], Suhyun Bang[1], Tae-Hyeon Kim[1], Dong Keun Lee[1], Chae Soo Kim[1], Kyungho Hong[1], Seongjae Cho[2], and Byung-Gook Park[1] *[1]Inter-University Semiconductor Research Center (ISRC) and the Department of Electrical and Computer Engineering, Seoul National University, [2]Department of Electronics Engineering, Gachon University*
TD2-G-3 11:30~11:45	**Atomistic Study on Electronic Structures of Perovskite Heterojunctions: Enhancing Optical Properties with Light-induced Phase Separation** Hoon Ryu *KISTI*
TD2-G-4 11:45~12:00	**Modeling of the Conductive Oxygen Vacancies in the HfO$_2$ Supercell based on the First Principles Calculation** Junsung Park and Sung-min Hong *School of Electrical Engineering and Computer Science, GIST*
TD2-G-5 12:00~12:15	**Intrinsic Limit of Contact Resistance in PtSe$_2$ Mono-Multilayer Heterostructure** Eun Yeong Yang, Jae Eun Seo, Dongwook Seo, and Jiwon Chang *UNIST*
TD2-G-6 12:15~12:30	**Tunneling Electroresistance Effect Enhanced by Polar Interface in Hafniabased Ferroelectric Tunnel Junction** Junbeom Seo and Mincheol Shin *School of Electrical Engineering, KAIST*